DMN4030LK3

40V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = 25°C
40V	30mΩ @ V_{GS} = 10V	13.7A
	50mΩ @ V_{GS} = 4.5V	10.6A

Features and Benefits

- Low on-resistance
- Fast switching speed
- **"Green" component and RoHS compliant (Note 1)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

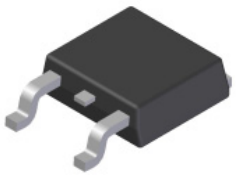
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

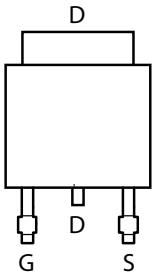
Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

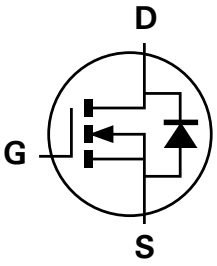
TO252-3L



TOP VIEW



PIN OUT -TOP VIEW



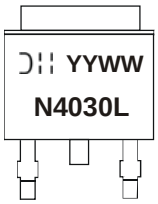
Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN4030LK3-13	N4030L	13	16	2,500

Notes: 1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



= Manufacturer's Marking
N4030L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01 - 53)

Maximum Ratings @T_A = 25°C unless otherwise specified

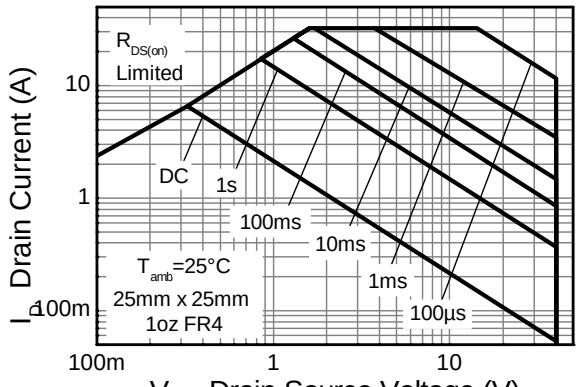
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	40	V
Gate-Source voltage		(Note 2)	V_{GS}	±20	V
Continuous Drain current	V_{GS} = 10V	(Note 4)	I_D	13.7	A
		T_A = 70°C (Note 4)		10.9	
		(Note 3)		9.4	
Pulsed Drain current	V_{GS} = 10V	(Note 5)	I_{DM}	37.7	A
Continuous Source current (Body diode)		(Note 4)	I_S	10.7	A
Pulsed Source current (Body diode)		(Note 5)	I_{SM}	37.7	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

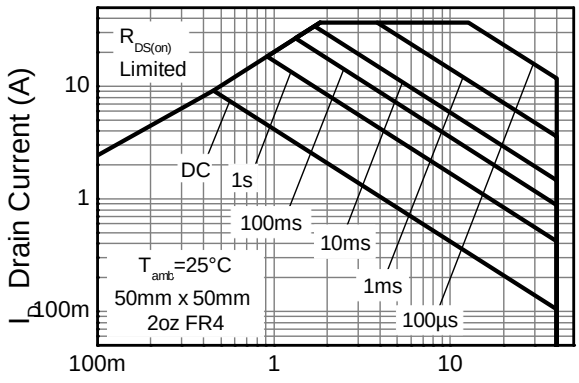
Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 3)	P_D	4.18 33.4	W mW/°C
	(Note 4)		8.9 71.4	
	(Note 6)		2.14 17.1	
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JA}$	29.9	°C/W
	(Note 4)		14.0	
	(Note 6)		58.4	
Thermal Resistance, Junction to Lead	(Note 7)	$R_{\theta JL}$	2.46	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

Notes:
2. AEC-Q101 V_{GS} maximum is ±16V.
3. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
4. Same as note 3, except the device is measured at t ≤ 10 sec.
5. Same as note 3, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
7. Thermal resistance from junction to solder-point (at the end of the drain lead).

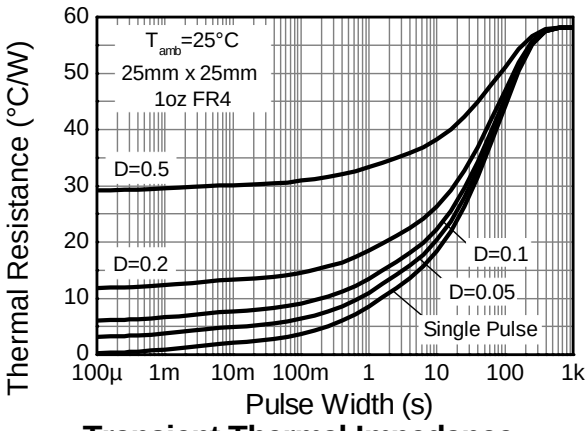
Thermal Characteristics



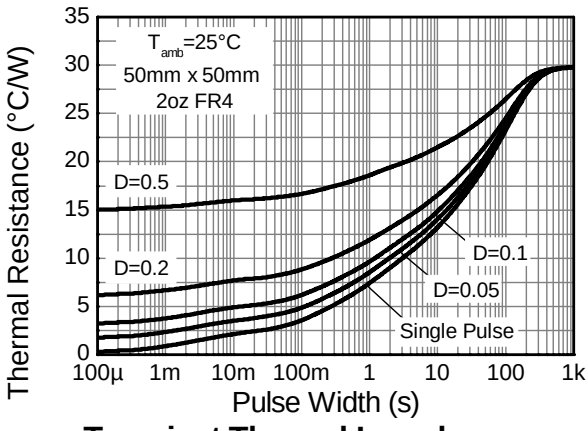
Safe Operating Area



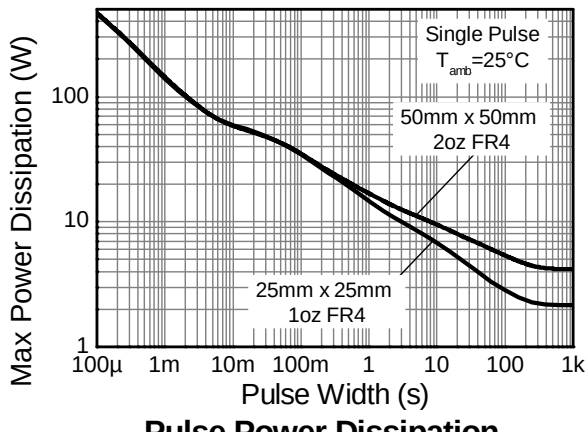
Safe Operating Area



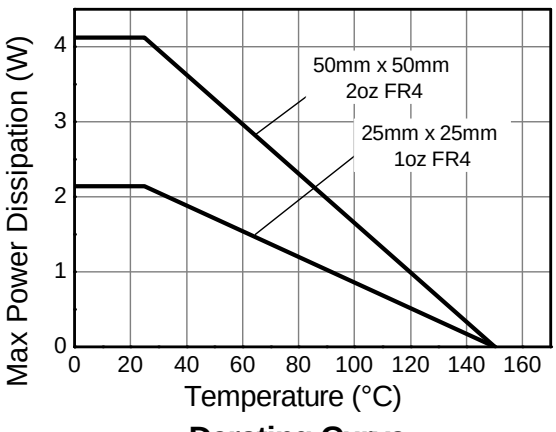
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



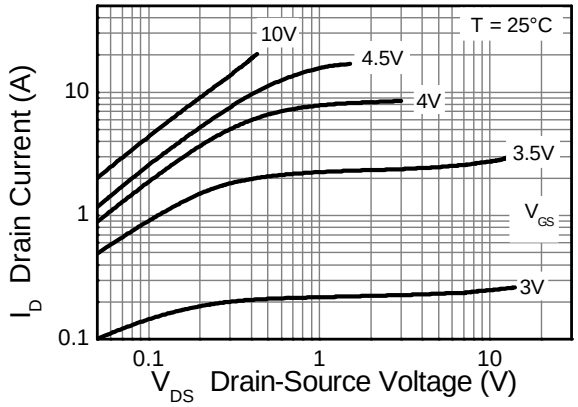
Derating Curve

Electrical Characteristics @T_A = 25°C unless otherwise specified

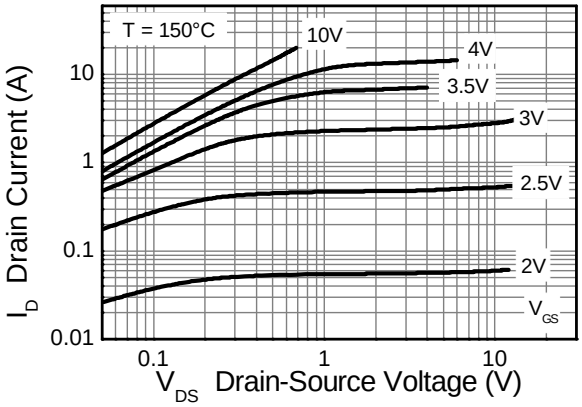
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	I_D = 250μA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	V_{DS} = 40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	I_D = 250μA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 8)	$R_{DS\ (ON)}$	—	0.021	0.030	Ω	V_{GS} = 10V, I_D = 12A
			0.037	0.050		V_{GS} = 4.5V, I_D = 6A
Forward Transconductance (Notes 8 & 9)	g_{fs}	—	22.8	—	S	V_{DS} = 15V, I_D = 12A
Diode Forward Voltage (Note 8)	V_{SD}	—	0.95	1.1	V	I_S = 12A, V_{GS} = 0V
Reverse recovery time (Note 9)	t_{rr}		135	—	ns	I_S = 12A, di/dt = 100A/μs
Reverse recovery charge (Note 9)	Q_{rr}	—	799	—	nC	
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	604	—	pF	V_{DS} = 20V, V_{GS} = 0V f= 1MHz
Output Capacitance	C_{oss}	—	106	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	59.6	—	pF	
Total Gate Charge (Note 10)	Q_g	—	6.5	—	nC	V_{GS} = 4.5V; V_{DS} = 20V, I_D = 12A
Total Gate Charge (Note 10)	Q_g	—	12.9	—	nC	V_{GS} = 10V; V_{DS} = 20V, I_D = 12A
Gate-Source Charge (Note 10)	Q_{gs}	—	2.3	—	nC	
Gate-Drain Charge (Note 10)	Q_{gd}	—	3.6	—	nC	
Turn-On Delay Time (Note 10)	$t_{D(on)}$	—	4.2	—	ns	V_{DD} = 20V, V_{GS} = 10V I_D = 12A, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 10)	t_r	—	12.4	—	ns	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	—	13.8	—	ns	
Turn-Off Fall Time (Note 10)	t_f	—	10.7	—	ns	

Notes:
8. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
9. For design aid only, not subject to production testing.
10. Switching characteristics are independent of operating junction temperatures.

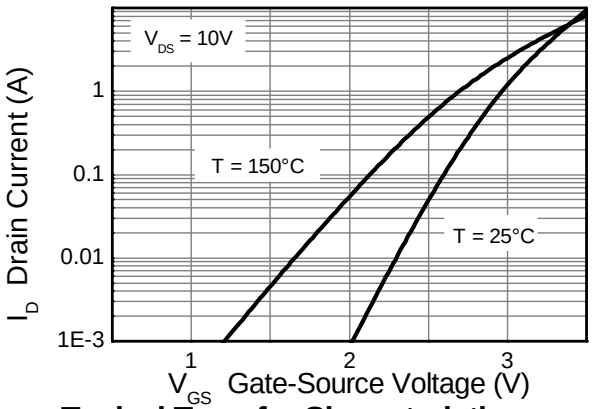
Typical Characteristics



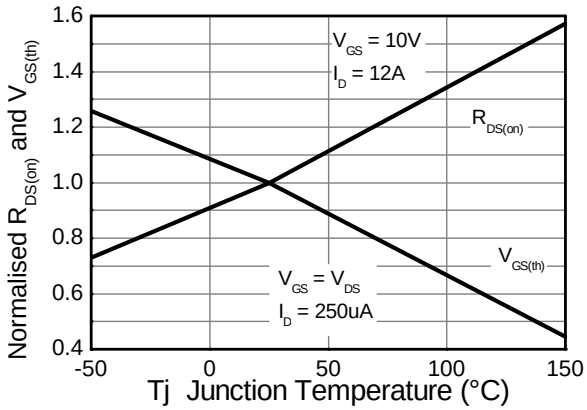
Output Characteristics



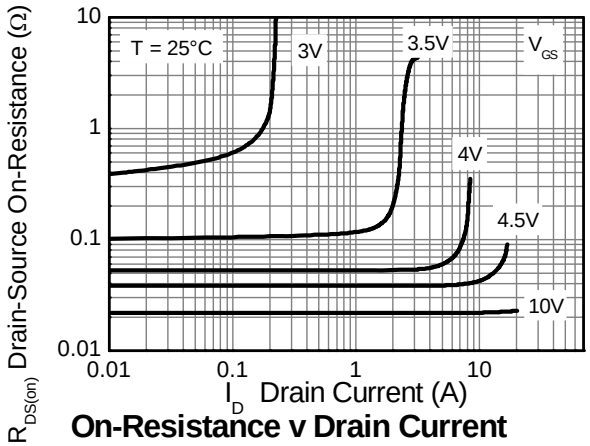
Output Characteristics



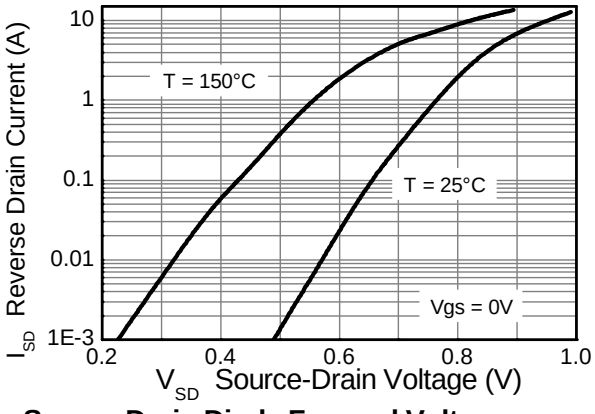
Typical Transfer Characteristics



Normalised Curves v Temperature

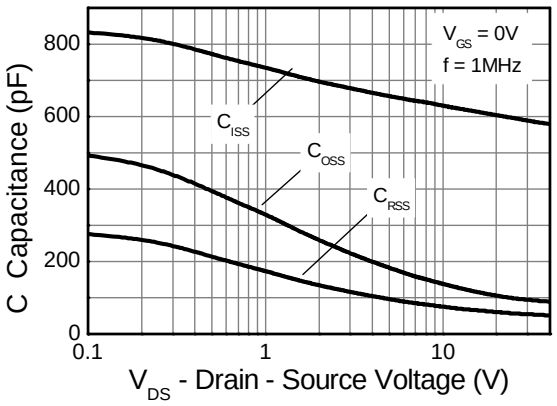


On-Resistance v Drain Current

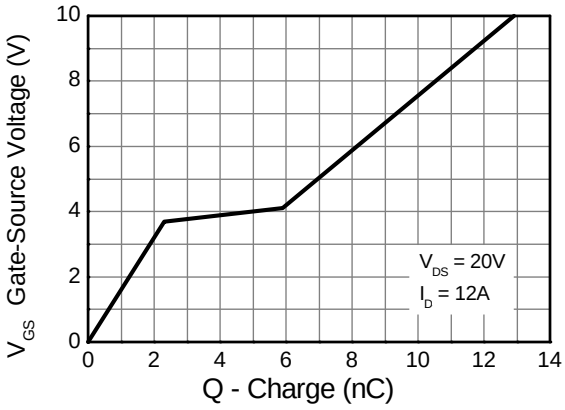


Source-Drain Diode Forward Voltage

Typical Characteristics - continued

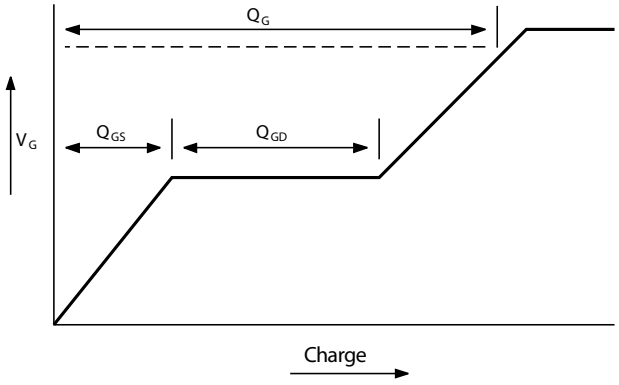


Capacitance v Drain-Source Voltage

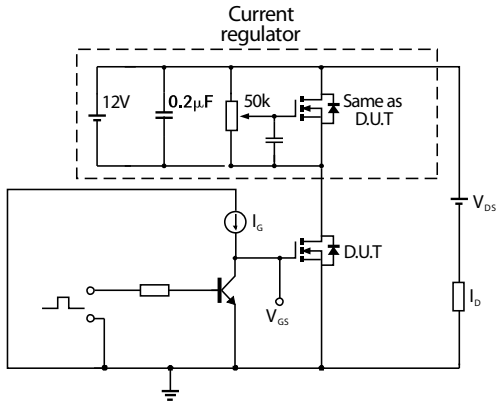


Gate-Source Voltage v Gate Charge

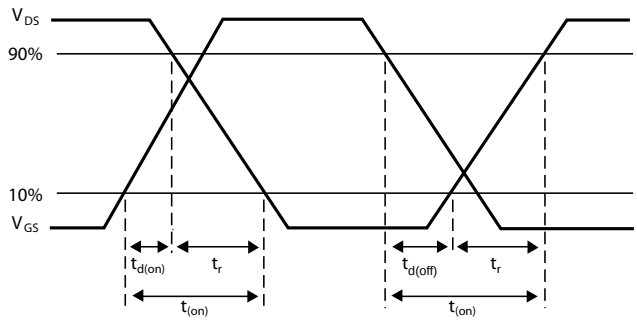
Test Circuits



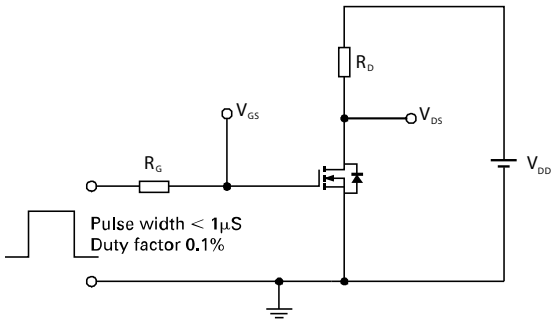
Basic gate charge waveform



Gate charge test circuit

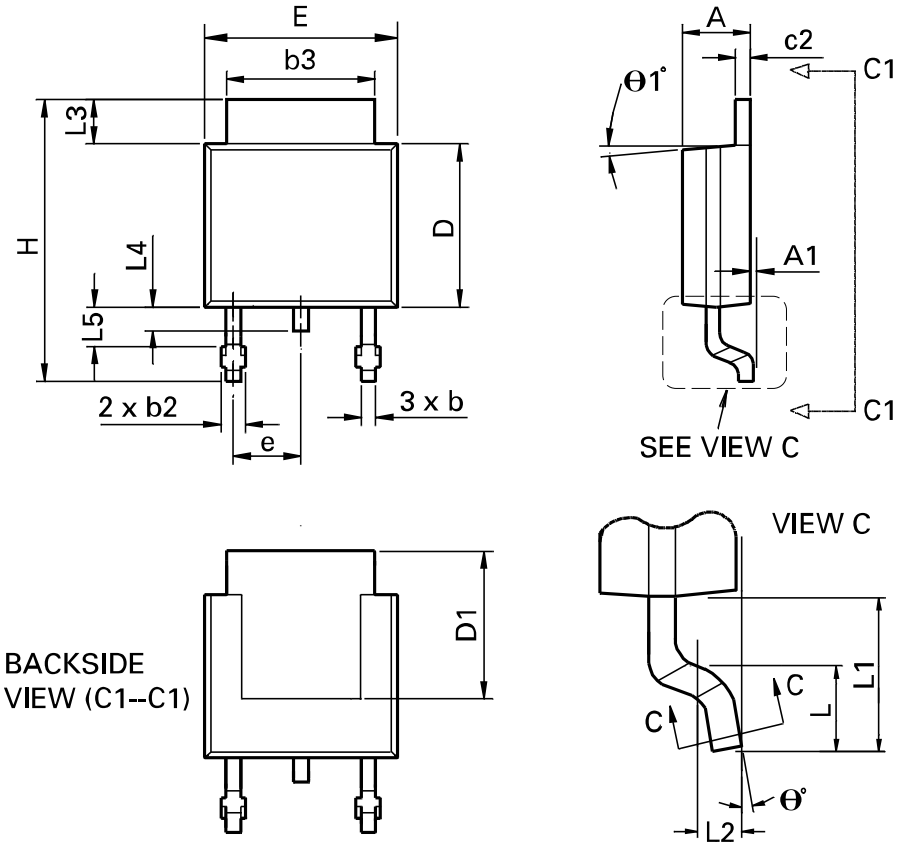


Switching time waveforms



Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Suggested Pad Layout